



# BT134-600

4Q Triac

21 November 2013

Product data sheet

## 1. General description

Planar passivated four quadrant triac in a SOT82 plastic package intended for use in general purpose bidirectional switching and phase control applications.

## 2. Features and benefits

- Compact package
- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control

## 4. Quick reference data

Table 1. Quick reference data

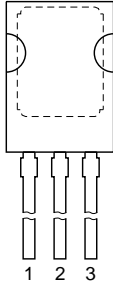
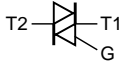
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	25	A
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	4	A
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	5	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	8	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	11	35	mA



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	30	70	mA

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>SIP3 (SOT82)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT134-600	SIP3	plastic single-ended package; 3 leads (in-line)	SOT82

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	4	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	25	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	27	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	3.1	$A^2s$
$di_T/dt$	rate of rise of on-state current	$I_T = 6\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $dI_G/dt = 0.2\text{ A}/\mu s$ ; T2+ G+	-	50	$A/\mu s$
		$I_T = 6\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $dI_G/dt = 0.2\text{ A}/\mu s$ ; T2+ G-	-	50	$A/\mu s$
		$I_T = 6\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $dI_G/dt = 0.2\text{ A}/\mu s$ ; T2- G-	-	50	$A/\mu s$
		$I_T = 6\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $dI_G/dt = 0.2\text{ A}/\mu s$ ; T2- G+	-	10	$A/\mu s$
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}C$
$T_j$	junction temperature		-	125	$^{\circ}C$

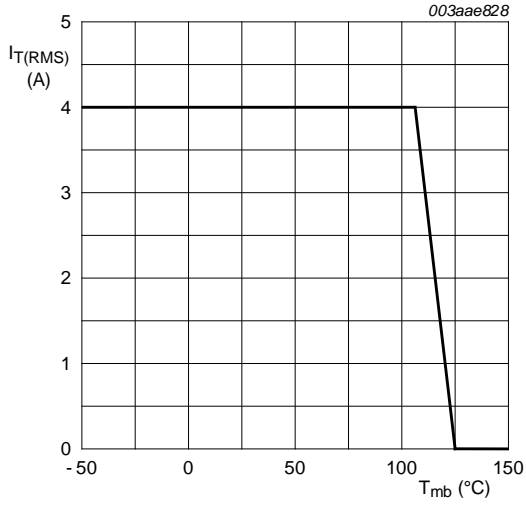
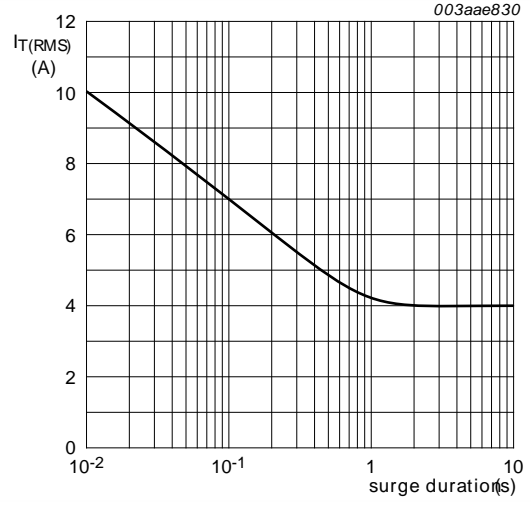
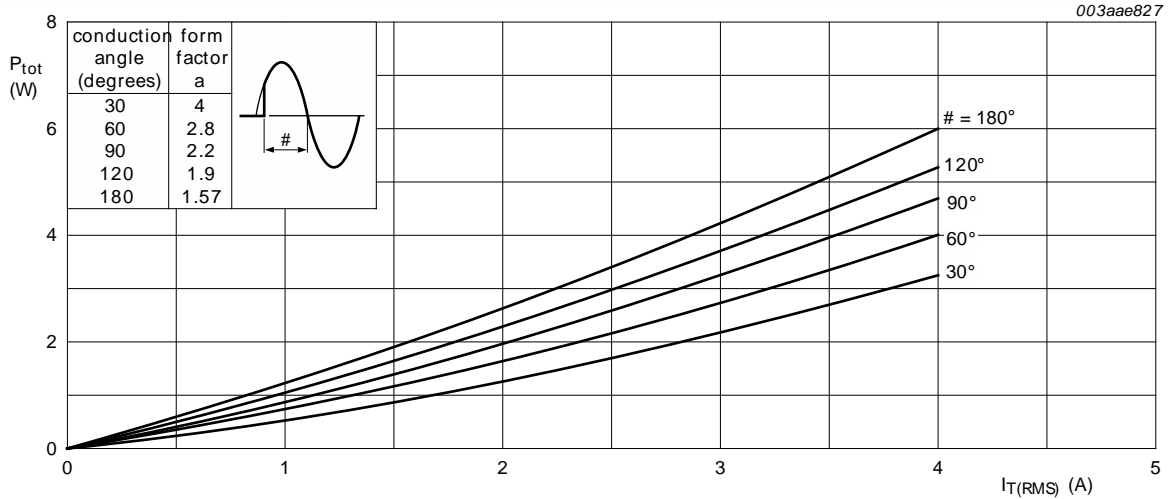


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



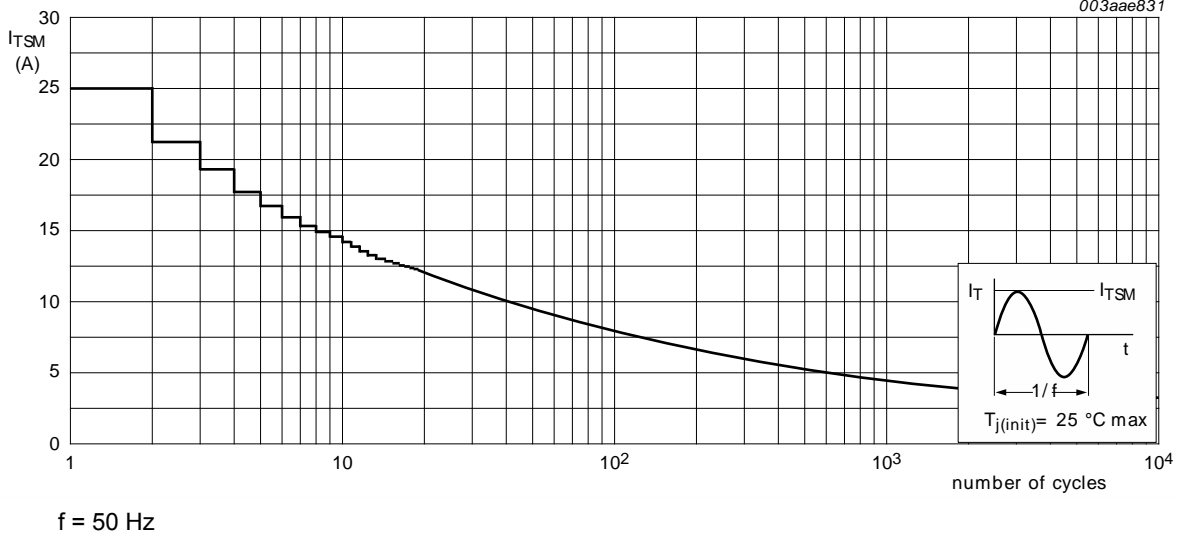
f = 50 Hz  
 $T_{mb} \leq 107\text{ }^\circ\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

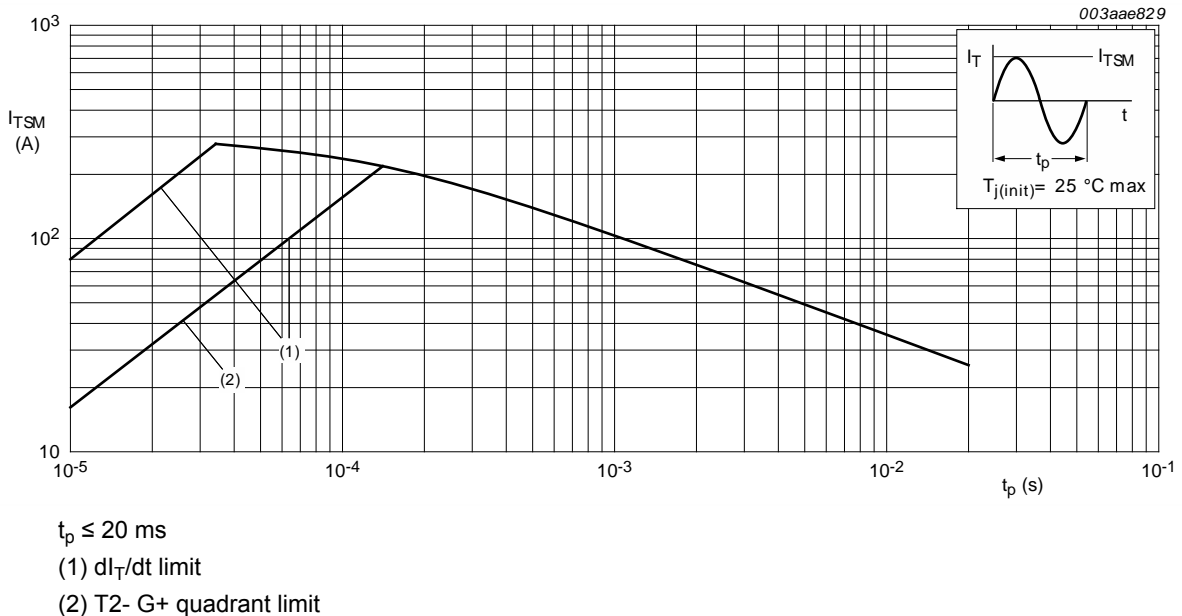


$\alpha$  = conduction angle  
 $a$  = form factor =  $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



**Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values**

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; <a href="#">Fig. 6</a>	-	-	3.7	K/W
		full cycle; <a href="#">Fig. 6</a>	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	100	-	K/W

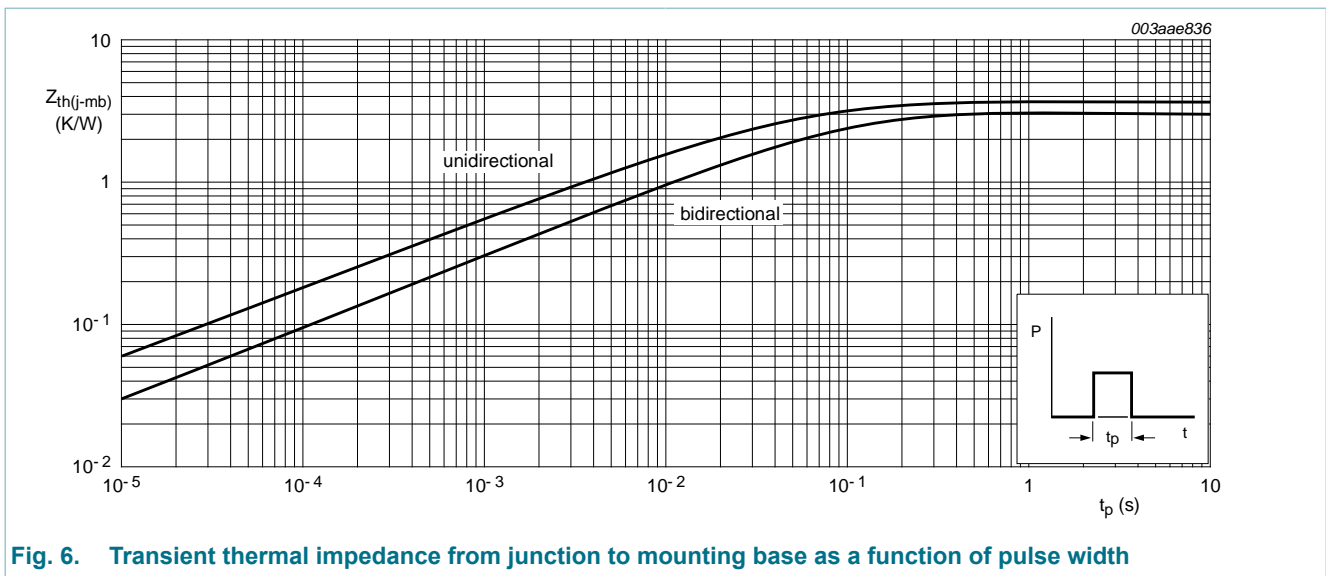
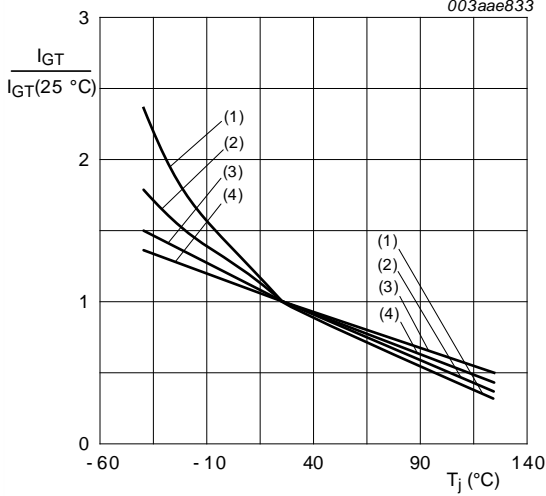


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	5	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	8	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	11	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	30	70	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	7	20	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	16	30	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	5	20	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	7	30	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	5	15	mA
$V_T$	on-state voltage	$I_T = 5\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	1.4	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	0.7	1	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ °C}$ ; <a href="#">Fig. 11</a>	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 600\text{ V}$ ; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	100	250	-	V/ $\mu$ s
$dV_{com}/dt$	rate of change of commutating voltage	$V_D = 400\text{ V}$ ; $T_j = 95\text{ °C}$ ; $dI_{com}/dt = 1.8\text{ A/ms}$ ; $I_T = 4\text{ A}$ ; gate open circuit	-	50	-	V/ $\mu$ s
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 6\text{ A}$ ; $V_D = 600\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	$\mu$ s



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

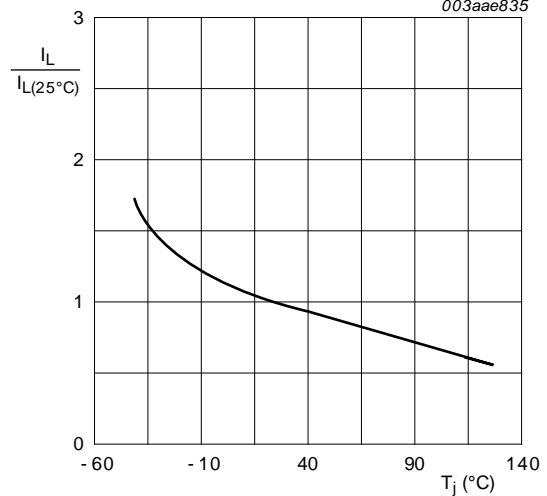


Fig. 8. Normalized latching current as a function of junction temperature

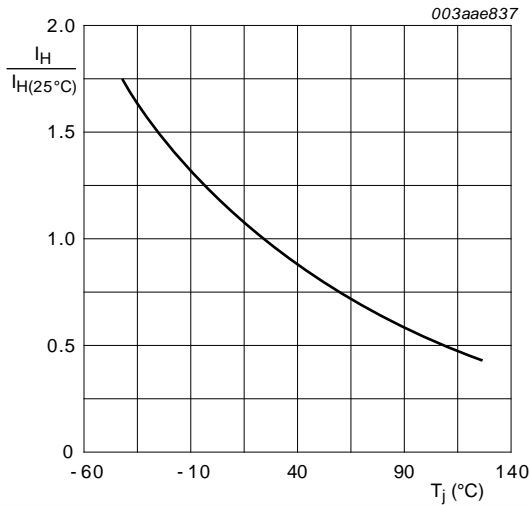
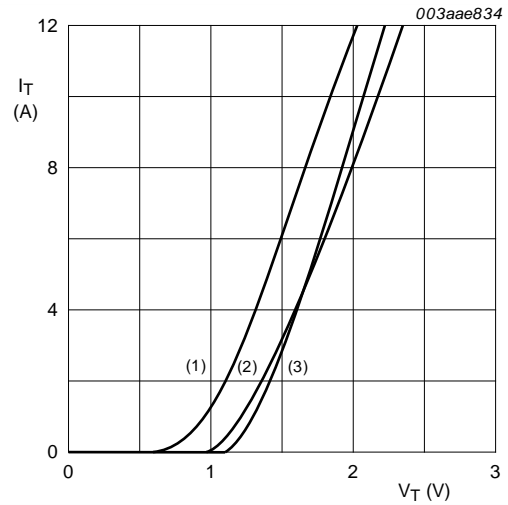


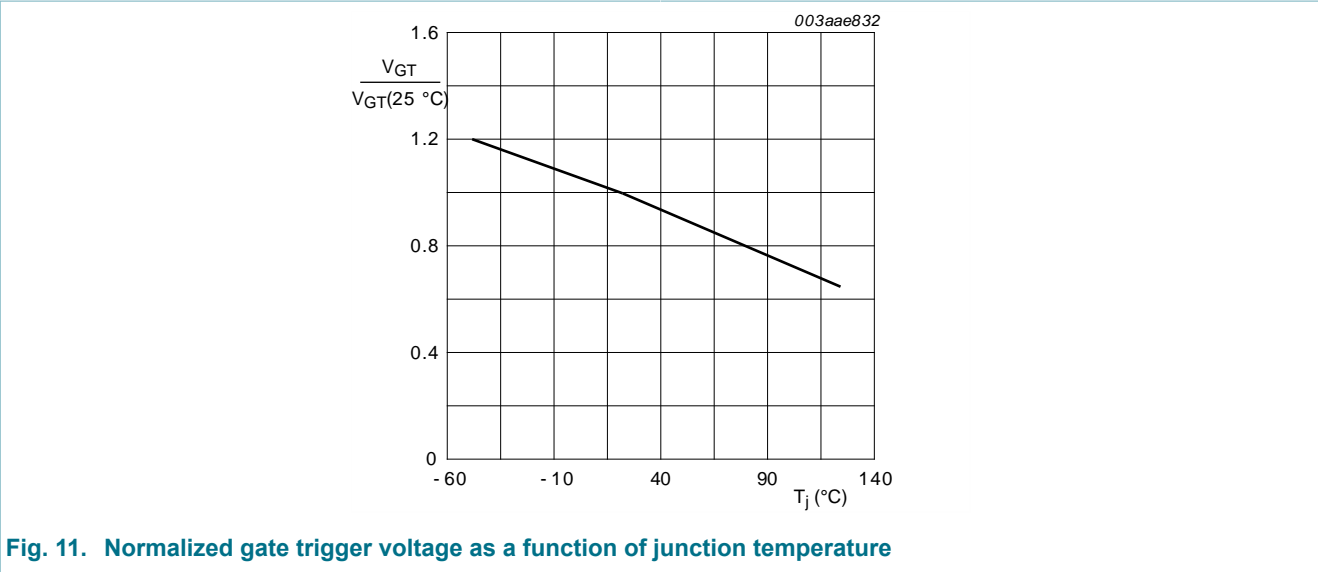
Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.27\text{ V}$
- $R_s = 0.091\ \Omega$
- (1)  $T_j = 125^\circ\text{C}$ ; typical values
- (2)  $T_j = 125^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage





### 10. Package outline

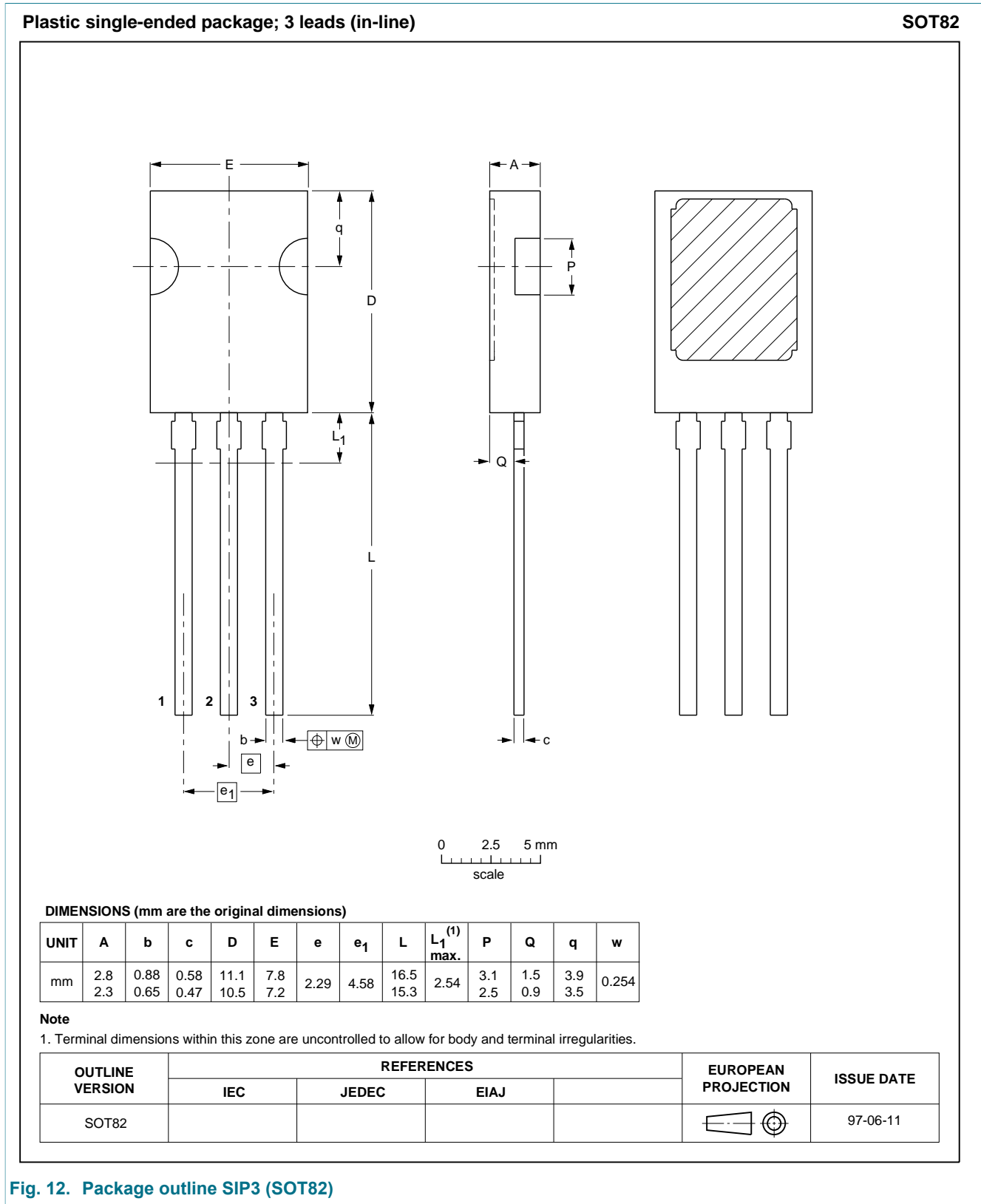


Fig. 12. Package outline SIP3 (SOT82)

## 11. Legal information

### 11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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